

# Lourdes G Salamanca-Riba

## List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Tunable mechanical behavior of graphene nanoribbon-metal composites fabricated through an electrocharge-assisted process. <i>Materials Science &amp; Engineering A: Structural Materials: Properties, Microstructure and Processing</i> , 2021, 800, 140289.	2.6	4
2	Electron beam-induced crystallization of Al <sub>2</sub> O <sub>3</sub> gate layer on $\hat{1}^2$ -Ga <sub>2</sub> O <sub>3</sub> MOS capacitors. <i>Micron</i> , 2021, 140, 102954.	1.1	8
3	Analytical electron microscopy of ( $2 \hat{A}^{-1} 01$ ) $\hat{1}^2$ -Ga <sub>2</sub> O <sub>3</sub> /SiO <sub>2</sub> and ( $2 \hat{A}^{-1} 01$ ) $\hat{1}^2$ -Ga <sub>2</sub> O <sub>3</sub> /Al <sub>2</sub> O <sub>3</sub> interface structures in MOS capacitors. <i>Journal of Applied Physics</i> , 2021, 129, 195705.	1.1	3
4	Transformation-Induced Magnetoelasticity in FeGa Alloys. <i>Advanced Engineering Materials</i> , 2019, 21, 1900399.	1.6	8
5	Millisecond synthesis of CoS nanoparticles for highly efficient overall water splitting. <i>Nano Research</i> , 2019, 12, 2259-2267.	5.8	85
6	Improving microstructural quantification in FIB/SEM nanotomography. <i>Ultramicroscopy</i> , 2018, 184, 24-38.	0.8	44
7	Analysis of the electronic and chemical structure in boron and phosphorus passivated $\langle i \rangle 4H \langle /i \rangle$ -SiC/SiO <sub>2</sub> interfaces using HRTEM and STEM-EELS. <i>Applied Physics Letters</i> , 2018, 113, .	1.5	6
8	$\langle i \rangle$ In Situ $\langle /i \rangle$ High Temperature Synthesis of Single-Component Metallic Nanoparticles. <i>ACS Central Science</i> , 2017, 3, 294-301.	5.3	34
9	Teaching an Old Material New Tricks: Easy and Inexpensive Focused Ion Beam (FIB) Sample Protection Using Conductive Polymers. <i>Microscopy and Microanalysis</i> , 2017, 23, 872-877.	0.2	3
10	FeS <sub>2</sub> Nanoparticles Embedded in Reduced Graphene Oxide toward Robust, High-Performance Electrocatalysts. <i>Advanced Energy Materials</i> , 2017, 7, 1700482.	10.2	144
11	Synthesis and characterization of copper-nanocarbon films with enhanced stability. <i>Carbon</i> , 2017, 122, 336-343.	5.4	9
12	Characterization of carbon nanostructures in Al and Ag covetic alloys. <i>Carbon</i> , 2017, 111, 309-321.	5.4	21
13	Near-Field Optical Properties of Fully Alloyed Noble Metal Nanoparticles. <i>Advanced Optical Materials</i> , 2017, 5, 1600568.	3.6	44
14	Long-Term Cr Poisoning Effect on LSCF-GDC Composite Cathodes Sintered at Different Temperatures. <i>Journal of the Electrochemical Society</i> , 2016, 163, F1091-F1099.	1.3	26
15	Sp <sup>2</sup> carbon embedded in Al-6061 and Al-7075 alloys in the form of crystalline graphene nanoribbons. <i>Carbon</i> , 2016, 107, 56-66.	5.4	28
16	Synthetic Alloys: Synthetic Crystals of Silver with Carbon: 3D Epitaxy of Carbon Nanostructures in the Silver Lattice ( <i>Adv. Funct. Mater.</i> 30/2015). <i>Advanced Functional Materials</i> , 2015, 25, 4746-4746.	7.8	0
17	Formation of nanometer-thick delaminated amorphous carbon layer by two-step plasma processing of methacrylate-based polymer. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2015, 33, .	0.6	8
18	Characterization of the Oxide-Semiconductor Interface in 4H-SiC/SiO <sub>2</sub> Structures using TEM and XPS. <i>Microscopy and Microanalysis</i> , 2015, 21, 1537-1538.	0.2	3

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19	Synthetic Crystals of Silver with Carbon: 3D Epitaxy of Carbon Nanostructures in the Silver Lattice. <i>Advanced Functional Materials</i> , 2015, 25, 4768-4777.	7.8	27
20	Three Dimensional Microstructural Characterization of Cathode Degradation in SOFCs Using FIB/SEM and TEM. <i>Microscopy and Microanalysis</i> , 2015, 21, 2161-2162.	0.2	3
21	Magnetization reversal in epitaxial highly anisotropic CoFe <sub>2</sub> O <sub>4</sub> hetero-structures. <i>Journal of Applied Physics</i> , 2015, 117, 17B727.	1.1	4
22	Nanocarbon-copper thin film as transparent electrode. <i>Applied Physics Letters</i> , 2015, 106, 193108.	1.5	14
23	In situ elevated temperature transmission electron microscopy of sensitized aluminum-magnesium alloy treated by ultrasonic impact treatment. <i>Journal of Materials Research</i> , 2014, 29, 1456-1462.	1.2	3
24	ZnO nanorod-smectic liquid crystal composites: Role of ZnO particle size, shape, and concentration on liquid crystal order and current-voltage properties. <i>Journal of Applied Physics</i> , 2014, 115, .	1.1	16
25	Temperature dependence of magnetic and magnetotransport properties in BiFeO <sub>3</sub> thin films by pulsed laser deposition. <i>Materials Research Society Symposia Proceedings</i> , 2014, 1636, 1.	0.1	0
26	Physical and Mechanical Characterization of a Nanocarbon Infused Aluminum-Matrix Composite. <i>Materials Performance and Characterization</i> , 2014, 3, 20130023.	0.2	6
27	Microstructural Evolution of Severely Plastically Deformed Sensitized Aluminum 5456-H116 Treated by Ultrasonic Impact Treatment. <i>Advanced Engineering Materials</i> , 2013, 15, 1105-1110.	1.6	6
28	Systematic structural and chemical characterization of the transition layer at the interface of NO-annealed 4H-SiC/SiO <sub>2</sub> metal-oxide-semiconductor field-effect transistors. <i>Journal of Applied Physics</i> , 2013, 113, .	1.1	31
29	PIEZORESPONSE FORCE MICROSCOPY STUDIES ON (100), (110) AND (111) EPITAXIALLY GROWTH BiFeO <sub>3</sub> THIN FILMS. <i>Materials Research Society Symposia Proceedings</i> , 2012, 1477, 7.	0.1	1
30	Magnetoelectric relaxation in rhombohedral LiNbO <sub>3</sub> -CoFe <sub>2</sub> O <sub>4</sub> . <i>Applied Physics Letters</i> , 2012, 100, .	1.5	6
31	Magnetic properties of Al doped TbMnO <sub>3</sub> thin films grown by pulsed laser deposition. <i>Journal of Applied Physics</i> , 2012, 112, .	1.1	7
32	Hexadecylamine capped silver and gold nanoparticles: Comparative study on formation and self-organization. <i>Materials Chemistry and Physics</i> , 2010, 123, 540-545.	2.0	35
33	Liquid crystal-ZnO nanoparticle photovoltaics: Role of nanoparticles in ordering the liquid crystal. <i>Applied Physics Letters</i> , 2010, 97, .	1.5	37
34	In Situ Observation of Reversible Nanomagnetic Switching Induced by Electric Fields. <i>Nano Letters</i> , 2010, 10, 1219-1223.	4.5	148
35	Synthesis and characterization of Nb <sub>2</sub> AlC thin films. <i>Thin Solid Films</i> , 2009, 517, 2920-2923.	0.8	47
36	Exchange bias in thin-film (Co/Pt) <sub>3</sub> /Cr <sub>2</sub> O <sub>3</sub> multilayers. <i>Journal of Magnetism and Magnetic Materials</i> , 2009, 321, 1955-1958.	1.0	34

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37	Flame Synthesis of Nanosized Cu <sup>2+</sup> Ce <sup>3+</sup> O, Ni <sup>2+</sup> Ce <sup>3+</sup> O, and Fe <sup>2+</sup> Ce <sup>3+</sup> O Catalysts for the Water-Gas Shift (WGS) Reaction. ACS Applied Materials & Interfaces, 2009, 1, 2624-2635.	4.0	46
38	Combinatorial discovery of a lead-free morphotropic phase boundary in a thin-film piezoelectric perovskite. Applied Physics Letters, 2008, 92, .	1.5	256
39	Role of oxygen partial pressure and seed layer chemistry in flux mediated epitaxy of single phase multiferroic BiFeO <sub>3</sub> thin films. Applied Physics Letters, 2008, 93, 192906.	1.5	7
40	Heteroepitaxially enhanced magnetic anisotropy in BaTiO <sub>3</sub> /CoFe <sub>2</sub> O <sub>4</sub> nanostructures. Applied Physics Letters, 2007, 90, 113113.	1.5	88
41	The Effects of Multiphase Formation on Strain Relaxation and Magnetization in Multiferroic BiFeO <sub>3</sub> Thin Films. Advanced Functional Materials, 2007, 17, 2594-2599.	7.8	42
42	Effects of a-Si:H resist vacuum-lithography processing on HgCdTe. Journal of Electronic Materials, 2006, 35, 1474-1480.	1.0	0
43	Fabrication of multiferroic epitaxial BiCrO <sub>3</sub> thin films. Applied Physics Letters, 2006, 88, 152902.	1.5	38
44	Microstructure and phase control in Bi <sup>2+</sup> Fe <sup>3+</sup> O multiferroic nanocomposite thin films. Applied Physics Letters, 2006, 88, 112505.	1.5	56
45	Reduction of laser-induced roughness in a-Si:H surfaces for vacuum compatible lithography. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2006, 24, 1684-1689.	0.9	1
46	Size and shape evolution of embedded single-crystal $\pm$ -Fe nanowires. Applied Physics Letters, 2005, 87, 203110.	1.5	14
47	Characterization of a-Si:H resists for a vacuum-compatible photolithography process. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2004, 22, 1141.	1.6	3
48	Suppression of antiphase domain boundary formation in Ba <sub>0.5</sub> Sr <sub>0.5</sub> TiO <sub>3</sub> films grown on vicinal MgO substrates. Applied Physics Letters, 2004, 85, 2905-2907.	1.5	13
49	Preferred orientation of DNA oligonucleotide probes on the (2 $\times$ 4) reconstructed surface of (001) GaAs. Journal of Applied Physics, 2004, 95, 6021-6024.	1.1	9
50	Self-assembled single-crystal ferromagnetic iron nanowires formed by decomposition. Nature Materials, 2004, 3, 533-538.	13.3	165
51	On the origin of high-temperature ferromagnetism in the low-temperature-processed Mn <sup>2+</sup> Zn <sup>2+</sup> O system. Nature Materials, 2004, 3, 709-714.	13.3	459
52	Processing and characterization of a-Si:H photoresists for a vacuum-compatible photolithography process. Journal of Electronic Materials, 2004, 33, 538-542.	1.0	1
53	Radiation-Induced Failure Mechanisms of GaAs-Based Biochips. IEEE Transactions on Device and Materials Reliability, 2004, 4, 192-197.	1.5	2
54	Evidence for power-law frequency dependence of intrinsic dielectric response in the CaCu <sub>3</sub> Ti <sub>4</sub> O <sub>12</sub> . Physical Review B, 2004, 70, .	1.1	110

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55	Three-dimensional heteroepitaxy in self-assembled BaTiO <sub>3</sub> /CoFe <sub>2</sub> O <sub>4</sub> nanostructures. Applied Physics Letters, 2004, 85, 2035-2037.	1.5	132
56	Multiferroic BaTiO <sub>3</sub> -CoFe <sub>2</sub> O <sub>4</sub> Nanostructures. Science, 2004, 303, 661-663.	6.0	2,051
57	Topochemical Anion Metathesis Routes to the Zr <sub>2</sub> N <sub>2</sub> S Phases and the Na <sub>2</sub> S and ACI Derivatives (A: Na, K). J. Appl. Phys. 101, 074301 (2007)	0.1	14
58	Topochemical Anion Metathesis Routes to the Zr <sub>2</sub> N <sub>2</sub> S Phases and the Na <sub>2</sub> S and ACI Derivatives (A = Na). J. Appl. Phys. 101, 074301 (2007)	0.0	17
59	InAs nanowires and whiskers grown by reaction of indium with GaAs. Applied Physics Letters, 2003, 82, 3749-3751.	1.5	43
60	Attachment of DNA probes on gallium arsenide surface. Applied Physics Letters, 2003, 83, 192-194.	1.5	23
61	Role of Pb excess in the crystallization of lead zirconate titanate films derived via sol-gel processing. Journal of Materials Research, 2003, 18, 1405-1411.	1.2	3
62	Systematic study of effects of growth conditions on the (nano-, meso-, micro)size and (one-, two-,) J. Appl. Phys. 94, 7749 (2003)	0.0	40
63	Ordering in (La,Sr)(Al,Ta)O <sub>3</sub> substrates. Journal of Materials Research, 2003, 18, 1698-1704.	1.2	26
64	Depth profile study of ferroelectric PbZr <sub>0.2</sub> Ti <sub>0.8</sub> O <sub>3</sub> films. Journal of Applied Physics, 2002, 92, 6762-6767.	1.1	15
65	Role of Ge on film quality of SiC grown on Si. Journal of Applied Physics, 2002, 91, 668-671.	1.1	13
66	Origin of antiphase domain boundaries and their effect on the dielectric constant of Ba <sub>0.5</sub> Sr <sub>0.5</sub> TiO <sub>3</sub> films grown on MgO substrates. Applied Physics Letters, 2002, 81, 4398-4400.	1.5	16
67	Low-temperature integration of lead-based ferroelectric capacitors on Si with diffusion barrier layer. Applied Physics Letters, 2002, 80, 3599-3601.	1.5	32
68	Magnetic Properties of Ultrathin Laminated Co/Cu Films Prepared by Electrodeposition. Journal of the Electrochemical Society, 2002, 149, C439.	1.3	30
69	Self-organized ordering in self-assembled quantum dot superlattices. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 88, 143-152.	1.7	13
70	Strain relaxation in AlSb/GaSb heterostructures. Solid-State Electronics, 2002, 46, 1643-1649.	0.8	6
71	Low-resistance Ti/Al/Ti/Au multilayer ohmic contact to n-GaN. Journal of Applied Physics, 2001, 89, 6214-6217.	1.1	92
72	Control of domain structure of epitaxial PbZr <sub>0.2</sub> Ti <sub>0.8</sub> O <sub>3</sub> thin films grown on vicinal (001) SrTiO <sub>3</sub> substrates. Applied Physics Letters, 2001, 79, 2805-2807.	1.5	28

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73	Dependence of dielectric properties on internal stresses in epitaxial barium strontium titanate thin films. Applied Physics Letters, 2001, 78, 2354-2356.	1.5	121
74	Structural Characterization of GaN Nanowires Fabricated via Direct Reaction of Ga Vapor and Ammonia. Materials Research Society Symposia Proceedings, 2001, 675, 1.	0.1	4
75	Atomic Force Microscopy and Transmission Electron Microscopy Study of Self-Organized Ordering in Vertically Aligned PbSe Quantum Dot Superlattices. Materials Research Society Symposia Proceedings, 2001, 696, 1.	0.1	1
76	Properties of GaN epitaxial layers grown on 6H-SiC(0001) by plasma-assisted molecular beam epitaxy. Journal of Electronic Materials, 2001, 30, 162-169.	1.0	34
77	The concept of high angle wedge polishing and thickness monitoring in TEM sample preparation. Ultramicroscopy, 2001, 88, 171-178.	0.8	14
78	TEM investigation of self-organized PbSe quantum dots as a function of spacer layer thickness and growth temperature. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 80, 104-107.	1.7	3
79	Growth of GaN on SiC(0001) by Molecular Beam Epitaxy. Physica Status Solidi A, 2001, 188, 595-599.	1.7	10
80	Phase diagram of lateral and vertical ordering in self-organized PbSe quantum dot superlattice grown MBE. Journal of Crystal Growth, 2001, 227-228, 1126-1131.	0.7	5
81	Growth of GaN nanowires by direct reaction of Ga with NH <sub>3</sub> . Journal of Crystal Growth, 2001, 231, 357-365.	0.7	113
82	Correlation Between Structural Imperfection and Giant Magnetoresistance in Electrodeposited Co/Cu Multilayers. Journal of the Electrochemical Society, 2001, 148, C518.	1.3	45
83	Role of Ga flux in dislocation reduction in GaN films grown on SiC(0001). Applied Physics Letters, 2001, 79, 3428-3430.	1.5	59
84	Growth and characterization of hexagonal (Zn,Mg)(S,Se) bulk substrates. Journal of Crystal Growth, 2000, 212, 83-91.	0.7	9
85	Nearly perfect 3D ordering in IV-VI quantum dot superlattices with ABCABC... vertical stacking sequence. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 7, 870-875.	1.3	9
86	Correlation between oxidation resistance and crystallinity of Ti-Al as a barrier layer for high-density memories. Acta Materialia, 2000, 48, 3387-3394.	3.8	23
87	SiC/Si(111) film quality as a function of GeH <sub>4</sub> flow in an MOCVD reactor. Journal of Electronic Materials, 2000, 29, 359-363.	1.0	4
88	TEM Study of Bulk AlN Growth by Physical Vapor Transport. MRS Internet Journal of Nitride Semiconductor Research, 2000, 5, 384-390.	1.0	0
89	Optimization of Bismuth Nanowire Arrays by Electrochemical Deposition. Materials Research Society Symposia Proceedings, 2000, 626, 1111.	0.1	0
90	Molecular-beam epitaxy growth and nitrogen doping of hexagonal ZnSe and ZnCdSe/ZnSe quantum well structures on hexagonal ZnMgSSe bulk substrates. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2000, 18, 1711.	1.6	10

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91	Optimized structural properties of wurtzite GaN on SiC(0001) grown by molecular beam epitaxy. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2000, 18, 1915-1918.	0.9	21
92	Tuning of Vertical and Lateral Correlations in Self-Organized PbSe/Pb <sub>1-x</sub> EuxTe Quantum Dot Superlattices. Physical Review Letters, 2000, 84, 4669-4672.	2.9	140
93	Electrical transport and magnetic properties of a possible electron-doped layered manganese oxide. Physical Review B, 2000, 61, 4141-4145.	1.1	5
94	Dielectric properties in heteroepitaxial Ba <sub>0.6</sub> Sr <sub>0.4</sub> TiO <sub>3</sub> thin films: Effect of internal stresses and dislocation-type defects. Applied Physics Letters, 2000, 77, 1695-1697.	1.5	237
95	Growth of large-scale GaN nanowires and tubes by direct reaction of Ga with NH <sub>3</sub> . Applied Physics Letters, 2000, 77, 3731-3733.	1.5	199
96	Formation of the (La <sub>0.67</sub> Sr <sub>0.33</sub> ) <sub>2</sub> MnO <sub>4</sub> Phase in La <sub>2</sub> Sr <sub>2</sub> Mn <sub>2</sub> O <sub>10</sub> Thin Films by Pulsed Laser Deposition. Journal of Materials Research, 2000, 15, 1524-1527.	1.2	4
97	The Effect of Ge on the Structure & Morphology of SiC Films Grown on (111) Si Substrates. Materials Science Forum, 2000, 338-342, 277-280.	0.3	1
98	TEM Study of the Morphology Of GaN/SiC (0001) Grown at Various Temperatures by MBE. MRS Internet Journal of Nitride Semiconductor Research, 2000, 5, 238-244.	1.0	1
99	Pulsed laser deposition of titanium nitride films on sapphire. Journal of Materials Research, 1999, 14, 3298-3302.	1.2	16
100	Thickness dependence of structural and electrical properties in epitaxial lead zirconate titanate films. Journal of Applied Physics, 1999, 86, 595-602.	1.1	144
101	Inversion of wurtzite GaN(0001) by exposure to magnesium. Applied Physics Letters, 1999, 75, 808-810.	1.5	187
102	Pulsed laser deposition and processing of wide band gap semiconductors and related materials. Journal of Electronic Materials, 1999, 28, 275-286.	1.0	30
103	Structural and magnetic properties of electrodeposited Co/Cu multilayers. Journal of Magnetism and Magnetic Materials, 1999, 198-199, 52-54.	1.0	25
104	Direct experimental study of the microscopic remagnetization mechanism in Co/Cu magnetic superlattices. Journal of Magnetism and Magnetic Materials, 1999, 198-199, 477-479.	1.0	4
105	Effect of Ge on SiC Film Morphology in SiC/Si Films Grown by MOCVD. Materials Research Society Symposia Proceedings, 1999, 572, 185.	0.1	0
106	Tem Investigation of Self-Organized Pbse Quantum Dots as a Function of Spacer Layer Thickness and Growth Temperature. Materials Research Society Symposia Proceedings, 1999, 583, 87.	0.1	0
107	TEM Study of the Morphology Of GaN/SiC (0001) Grown at Various Temperatures by MBE. Materials Research Society Symposia Proceedings, 1999, 595, 1.	0.1	0
108	TEM Study of Bulk AlN Growth by Physical Vapor Transport. Materials Research Society Symposia Proceedings, 1999, 595, 1.	0.1	2

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109	Tem Investigation of Growth Temperature Dependence in Pulsed-Laser Ablated PLZT Films for Pyroelectric Applications. Materials Research Society Symposia Proceedings, 1999, 596, 563.	0.1	0
110	Cation Ordering Structure in La <sub>0.8</sub> Ca <sub>0.2</sub> MnO <sub>3</sub> Thin Films by Pulsed Laser Deposition. Materials Research Society Symposia Proceedings, 1999, 602, 81.	0.1	0
111	Growth of GaAsN/GaAs, GalnAsN/GaAs and GalnAsN/GaAs quantum wells by low-pressure organometallic chemical vapor deposition. Journal of Crystal Growth, 1998, 195, 427-437.	0.7	77
112	Fabrication and characterization of epitaxial AlN/TiN bilayers on sapphire. Thin Solid Films, 1998, 323, 37-41.	0.8	33
113	Advances in pulsed laser deposition of nitrides and their integration with oxides. Applied Surface Science, 1998, 127-129, 431-439.	3.1	39
114	Structural and magnetic fourfold symmetry of Co/Cu multilayers electrodeposited on Si(001) substrates. Journal of Applied Physics, 1998, 84, 1504-1507.	1.1	23
115	Heteroepitaxy of ZnO on GaN and its implications for fabrication of hybrid optoelectronic devices. Applied Physics Letters, 1998, 73, 348-350.	1.5	425
116	Optical Phase and Amplitude Modulation in (9/65/35) Pb-La-Zr-Ti-O Thin Films. Materials Research Society Symposia Proceedings, 1998, 541, 753.	0.1	0
117	The Nanofabrication of Quantum Wires for the Next Generation of Thermoelectrics. Materials Research Society Symposia Proceedings, 1998, 545, 209.	0.1	2
118	Surface Reconstruction during Molecular Beam Epitaxial Growth of GaN (0001). MRS Internet Journal of Nitride Semiconductor Research, 1998, 3, 1.	1.0	60
119	Heteroepitaxial Growth Of ZnO Films BY PLD. Materials Research Society Symposia Proceedings, 1997, 474, 383.	0.1	1
120	Growth Mechanism and Structure of Aln Films Grown on Sapphire by MOCVD. Materials Research Society Symposia Proceedings, 1997, 482, 229.	0.1	3
121	The Reduction of The Defect Density in CdTe Buffer Layers for The Growth of HgCdTe Infrared Photodiodes on Si (211) Substrates. Materials Research Society Symposia Proceedings, 1997, 484, 329.	0.1	1
122	The Reduction of The Defect Density in CdTe Buffer Layers for The Growth of HgCdTe Infrared Photodiodes on Si (211) Substrates. Materials Research Society Symposia Proceedings, 1997, 487, 607.	0.1	2
123	Microstructure Investigations and Structure-Property Correlations in Ferroelectric thin film Capacitors. Materials Research Society Symposia Proceedings, 1997, 493, 171.	0.1	1
124	Unusual Metal-Insulator Transitions in the LaTi <sub>1-x</sub> V <sub>x</sub> O <sub>3</sub> Perovskite Phases. Chemistry of Materials, 1996, 8, 418-427.	3.2	16
125	Magnetoresistive Properties of Quasiperiodic Metallic Multilayers. Materials Research Society Symposia Proceedings, 1996, 451, 419.	0.1	5
126	Structure and Morphology of MBE Fabricated Zn <sub>0.5</sub> Fe <sub>0.5</sub> Se On GaAs as a Function of Substrate Preparation and Growth Temperature. Materials Research Society Symposia Proceedings, 1996, 441, 139.	0.1	0



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127	Comparison of the Microstructure of AlN Films Grown by MOCVD and by PLD on Sapphire Substrates. Materials Research Society Symposia Proceedings, 1996, 449, 453.	0.1	1
128	Structural Characteristics of MOCVD Grown AlN Films with Different Carbon Concentration. Materials Research Society Symposia Proceedings, 1996, 449, 555.	0.1	1
129	Observation of [100] and [010] dark line defects in optically degraded znse-based leds by transmission electron microscopy. Journal of Electronic Materials, 1996, 25, 239-243.	1.0	3
130	Very low defect density ZnSe grown on GaAs by atmospheric pressure metal organic chemical vapor deposition. Materials Chemistry and Physics, 1996, 45, 88-91.	2.0	2
131	Growth and characterization of II-VI blue light-emitting diodes using short period superlattices. Applied Physics Letters, 1996, 68, 379-381.	1.5	32
132	Heteroepitaxy of CdTe on {211} Si using crystallized amorphous ZnTe templates. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1996, 14, 2366.	1.6	47
133	Observation of <100> Dark Line Defects in Optically Degraded ZnSxSe1-x-based Light Emitting Diodes by Transmission Electron Microscopy. Japanese Journal of Applied Physics, 1996, 35, 5333-5337.	0.8	1
134	Ion-Assisted Pulsed Laser Deposition of BN Films. Materials Research Society Symposia Proceedings, 1995, 388, 165.	0.1	0
135	Double Periodicity Formation in EuTe/PbTe Superlattices. Materials Research Society Symposia Proceedings, 1995, 399, 543.	0.1	3
136	Misfit strain induced tweed-twin transformation on composition modulation Zn1-xMgxSxSe1-y layers and the quality control of the ZnSe buffer/GaAs interface. Journal of Electronic Materials, 1995, 24, 155-162.	1.0	13
137	Wide band gap MgZnSse grown on (001) GaAs by molecular beam epitaxy. Applied Physics Letters, 1995, 66, 3462-3464.	1.5	19
138	Characteristics of oxygen over-reduced Nd1.85Ce0.15CuO4-y films. Applied Physics Letters, 1995, 66, 2137-2139.	1.5	15
139	On the generation of a cross grid of extended screw-type misfit dislocations on the ZnS<sub>x</sub>/Se<sub>1-x</sub>/GaAs interface. Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties, 1995, 71, 883-899.	0.8	4
140	Generation of degradation defects, stacking faults, and misfit dislocations in ZnSe-based films grown on GaAs. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1995, 13, 1694.	1.6	89
141	Chemical Ordering: A New Direction in Diluted Magnetic Semiconductors. Materials Science Forum, 1995, 182-184, 435-442.	0.3	1
142	Giant magnetoresistance of electrodeposited CoNiCu/Cu multilayers. Scripta Metallurgica Et Materialia, 1995, 33, 1643-1646.	1.0	17
143	Dependence of the density and type of stacking faults on the surface treatment of the substrate and growth mode in ZnSxSe1-x/ZnSe buffer layer/GaAs heterostructures. Applied Physics Letters, 1995, 67, 3298-3300.	1.5	70
144	Dislocation nucleation mechanism in nitrogen-doped ZnSe/GaAs. Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties, 1994, 69, 301-313.	0.8	17

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146	Giant magnetoresistance peaks in CoNiCu/Cu multilayers grown by electrodeposition. Journal of Applied Physics, 1994, 76, 6519-6521.	1.1	56
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